參考文獻

- B.G. Streetman and S. Banerjee, Solid State Electronic Devices, 5th edition, Prentice 1 Hall. New Jersey, 2000.
- D.A. Neamen, Semiconductor Physics and Devices, 2nd edition, McGraw-Hill, New 2 York, 1992.
- S.M. Sze, Semiconductor Devices-Physics and Technology, 2nd edition, Wiley, New 3 York, 2001.
- R.S. Muller and T.I. Kamins, Device Electronics for Integrated Circuits, 3rd edition, 4 Wiley, New York, 2003.
- D.A. Neamen, An Introduction to Semiconductor Devices, McGraw-Hill, New 5 York, 2006.
- S. Wolf, Silicon Processing for the VLSI Era Volume III-The Submicron MOSFET, 6 Lattice Press, CA, 1995.
- 7 J.E. Chung et al., "Performance and Reliability Design Issues for Deep-Submicrometer MOSFET's," IEEE Trans. Electron Dev., ED-38, 545 (1991).
- M.C. Jeng et al., "Performance and Hot-Electron Reliability of Deep-Submicron 8 MOSFETs, "IEDM, 1987, p.710-713.
- 9 W. Fichtner et al., "Optimized MOSFETs with Subquartermicron Channel Lengths," IEDM, 1983, p.384-387.
- 10 J.R. Brews et al., "Generalized Guide for MOSFET Miniaturization," IEEE Electron Dev. Lett., EDL-1, 2 (1980).
- 11 D.M. Caughey and R.E. Thomas, "Carrier Mobilities in Silicon Empirically Related to Doping and Field," Proc. IEEE, 55, 2192 (1967).
- 12 R.W. Coen and R.S. Muller, "Velocity of Surface Carriers in Inversion Layers on Silicon," Solid-State Electron., 23, 35 (1980).
- 13 Y. Taur et al., "Saturation Transconductance of Deep-Submicron-Channel MOSF-ETs," Solid-State Electron., 36, 1085 (1993).
- 14 C.G. Sodini, P.K. Ko, and J.L. Moll, "The Effect of High Fields on MOS Device and Circuit Performance," IEEE Trans. Electron Dev., ED-31, 1386 (1984).